

### Vishay High Power Products

## **HEXFRED® Ultrafast Soft Recovery Diode, 210 A**





	Bas
LF-PAK (D-67)	catho

PRODUCT SUMMARY				
I <sub>F</sub> (maximum)	210 A			
$V_{R}$	400 V			
I <sub>F(DC)</sub> at T <sub>C</sub>	106 A at 100 °C			

#### **FEATURES**

- Very low Q<sub>rr</sub> and t<sub>rr</sub>
- · Lead (Pb)-free
- · Designed and qualified for industrial level



#### **BENEFITS**

- · Reduced RFI and EMI
- · Reduced snubbing

#### **DESCRIPTION**

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and dl/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	$V_R$		400	V	
Continuous forward current		T <sub>C</sub> = 25 °C	210		
Continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	106	Α	
Single pulse forward current	I <sub>FSM</sub>	Limited by junction temperature	600		
Non-repetitive avalanche energy	E <sub>AS</sub>	$L = 100 \mu H$ , duty cycle limited by maximum $T_J$	1.4	mJ	
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C 329		W	
Maximum power dissipation		T <sub>C</sub> = 100 °C	132	VV	
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C	

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	$V_{BR}$	I <sub>R</sub> = 100 μA		400	-	-	
		I <sub>F</sub> = 90 A		-	1.06	1.45	V
Maximum forward voltage	$V_{FM}$	I <sub>F</sub> = 180 A	See fig. 1	-	1.2	1.67	
		I <sub>F</sub> = 90 A, T <sub>J</sub> = 125 °C		-	0.96	1.23	
Maximum reverse leakage current	I <sub>RM</sub>	T <sub>J</sub> = 125 °C, V <sub>R</sub> = 400 V	See fig. 2	-	0.6	2	mA
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	=	180	260	pF
Series inductance	L <sub>S</sub>	From top of terminal hole to mounting plane		1	7.0	-	nΗ

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### HFA90NH40PbF

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		T <sub>J</sub> = 25 °C		-	90	140	20	
See fig. 5	t <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	158	240	ns	
Peak recovery current	IRRM	T <sub>J</sub> = 25 °C		-	9	17	Α	
See fig. 6		IRRM	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 90 A dI <sub>F</sub> /dt = 200 A/μs	-	15	30	A
Reverse recovery charge	0	T <sub>J</sub> = 25 °C	T 05 00   ' '	$V_{\rm R} = 200 \text{ V}$	-	420	1100	nC
See fig. 7	Q <sub>rr</sub>	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C	-11 -22	-	1200	3200	110
Peak rate of recovery current	al /at	T <sub>J</sub> = 25 °C		-	370	-	Δ/110	
See fig. 8	dI <sub>(rec)M</sub> /dt	T <sub>J</sub> = 125 °C		-	270	-	A/μs	

THERMAL - MECHAN	ICAL SPE	CIFICAT	IONS		
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T <sub>J</sub> , T <sub>Stg</sub>		- 55 to 150	°C
Maximum thermal resistance, junction to case		R <sub>thJC</sub>	DC operation See fig. 4	0.38 0.05	
Typical thermal resistance, case to heatsink		R <sub>thCS</sub>	Mounting surface, flat, smooth and greased		
Approximate weight				30	g
Approximate weight				1.06	oz.
Mounting torque	minimum		Non-lubricated threads	3 (26.5)	
Mounting torque	maximum			4 (35.4)	N⋅m
Tin-dis-	minimum			3.4 (30)	(lbf · in)
Terminal torque — maxin				5 (44.2)	1
Case style			HALF-PAK module		•

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## HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 210 A

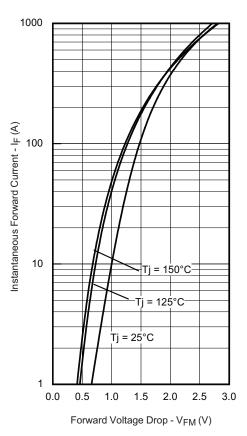


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

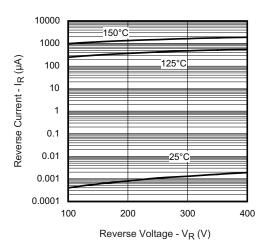


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

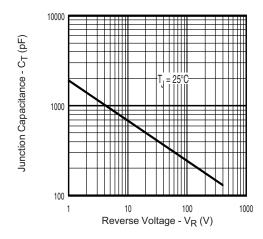


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

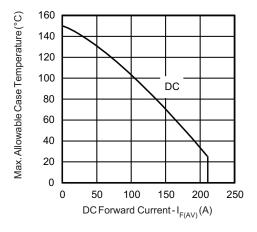


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

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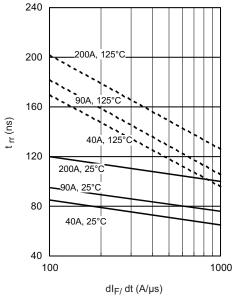


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

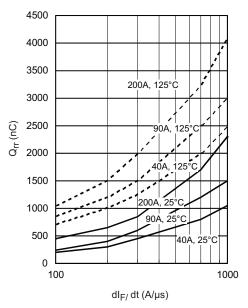


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

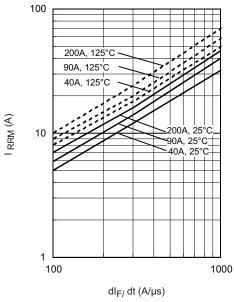


Fig. 6- Typical Recovery Current vs. dI<sub>F</sub>/dt

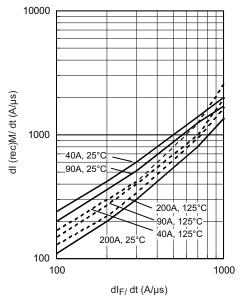


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 



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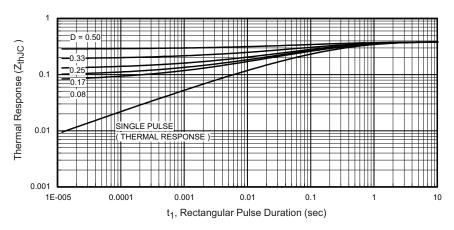


Fig. 9 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (Per Leg)

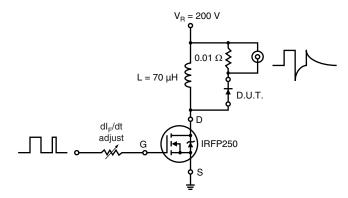
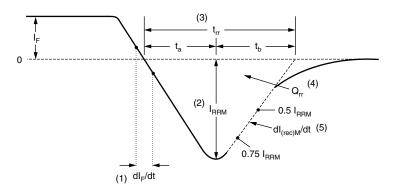


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{\text{RRM}}$ 
  - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5)  $dl_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 11 - Reverse Recovery Waveform and Definitions

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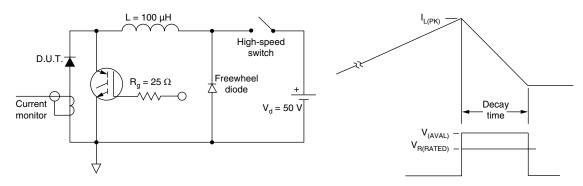


Fig. 12 - Avalanche Test Circuit and Waveforms

#### **ORDERING INFORMATION TABLE**

Device code

HFA 90 N H 40 PbF

1 2 3 4 5 6

1 - HEXFRED® family
2 - Average current rating

3 - N = Not isolated4 - H = HALF-PAK

5 - Voltage rating (400 V)

6 - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS		
Dimensions	http://www.vishay.com/doc?95020	

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